

MA2B150, MA2B161, MA2B162, MA2B162A

Silicon epitaxial planar type

For switching circuits

■ Features

- Short reverse recovery time t_{rr}
- Small terminal capacitance, C_t

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter		Symbol	Rating	Unit
Reverse voltage (DC)	MA2B150	V_R	35	V
	MA2B161		50	
	MA2B162		75	
	MA2B162A		120	
Repetitive peak reverse voltage	MA2B150	V_{RRM}	35	V
	MA2B161		50	
	MA2B162		75	
	MA2B162A		120	
Average forward current		$I_{F(AV)}$	100	mA
Repetitive peak forward current		I_{FRM}	225	mA
Non-repetitive peak forward surge current*		I_{FSM}	500	mA
Junction temperature		T_j	200	°C
Storage temperature		T_{stg}	-55 to +150	°C

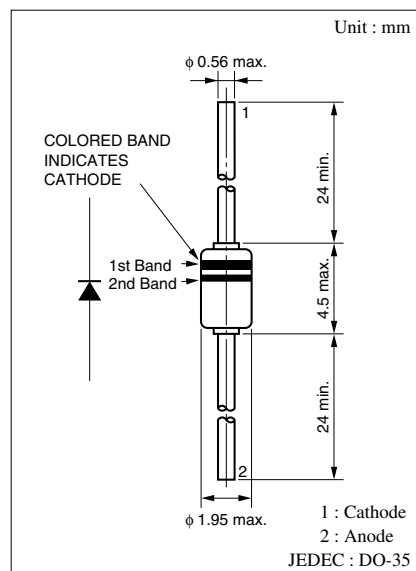
Note) * : $t = 1 \text{ s}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	MA2B150	I_R	$V_R = 15 \text{ V}$		0.025	μA
					0.1	
		I_R	$V_R = 30 \text{ V}$		0.025	
					5	
	MA2B161	I_R	$V_R = 15 \text{ V}$		0.025	
					5	
		I_R	$V_R = 50 \text{ V}$		0.012	
					5	
	MA2B162	I_R	$V_R = 20 \text{ V}$		0.012	
					5	
		I_R	$V_R = 75 \text{ V}$		0.012	
					5	
Forward voltage (DC)	MA2B162A	V_F	$I_F = 100 \text{ mA}$		0.95	V
					1.2	
					0.95	
					1.2	
					0.95	
					1.2	
					0.95	
					1.2	
Reverse voltage (DC)	MA2B150	V_R	$I_R = 5 \mu\text{A}$	35		V
Terminal capacitance		C_t	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$	0.9	2	pF
Reverse recovery time*	MA2B150	t_{rr}	$I_F = 10 \text{ mA}, V_R = 1 \text{ V}, R_L = 100 \Omega$ Measure when $I_{rr} = 0.1 \cdot I_R$		10	ns
	MA2B161/162/162A			2.2	4	

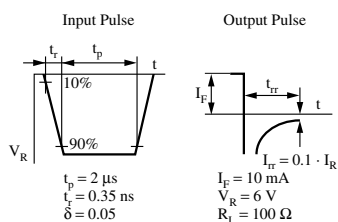
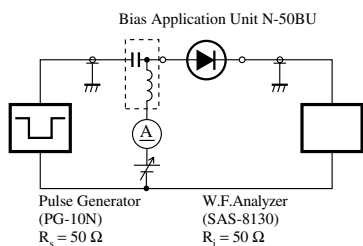
■ Cathode Indication

Type No.		MA2B150	MA2B161	MA2B162	MA2B162A
Color	1st Band	White	Green	Violet	Black
	2nd Band	——	——	——	Black



Note) 1. Rated input/output frequency:
100 MHz

2. * : t_{rr} measuring circuit


 t_r measuring circuit
